

Description

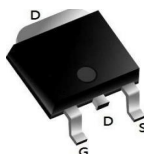
The 20N03 is the high cell density trench N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The 20N03 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved

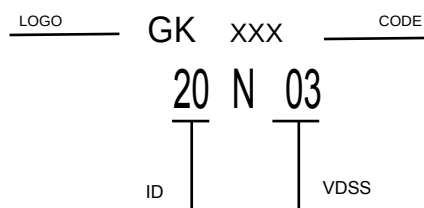
Features

Super Low Gate Charge
100% EAS Guaranteed
Green Device Available
Excellent CdV/dt effect decline
Advanced high cell density Trench technology

TO-252



V_{DS} 30 V
 I_D 20 A
 $R_{DS(ON)}$ 15mΩ



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	30		V
V_{GS}	Gate-Source Voltage	±20		V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	20		A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	8		A
I_{DM}	Pulsed Drain Current ²	38		A
EAS	Single Pulse Avalanche Energy ³	28		mJ
I_{AS}	Avalanche Current	13.8		A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	5.5		W
T_{STG}	Storage Temperature Range	-55 to 175		°C
T_J	Operating Junction Temperature Range	-55 to 175		°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	36	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} = 0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =5A	-	15	20	mΩ
		V _{GS} =4.5V, I _D =3A	-	21	29	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	490	-	pF
C _{oss}	Output Capacitance		-	79	-	pF
C _{rss}	Reverse Transfer Capacitance		-	61	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =5.8A, V _{GS} =10V	-	10	-	nC
Q _{gs}	Gate-Source Charge		-	1.7	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	2.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, I _D =3A, V _{GS} =10V, R _{REN} =3Ω	-	6	-	ns
t _r	Turn-on Rise Time		-	15	-	ns
t _{d(off)}	Turn-off Delay Time		-	17	-	ns
t _f	Turn-off Fall Time		-	17	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	9	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	36	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =9A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =5A, dI/dt=100A/μs	-	7	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	2	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=15V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}=6A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

RATING AND CHARACTERISTIC CURVES

Figure 1: Output Characteristics

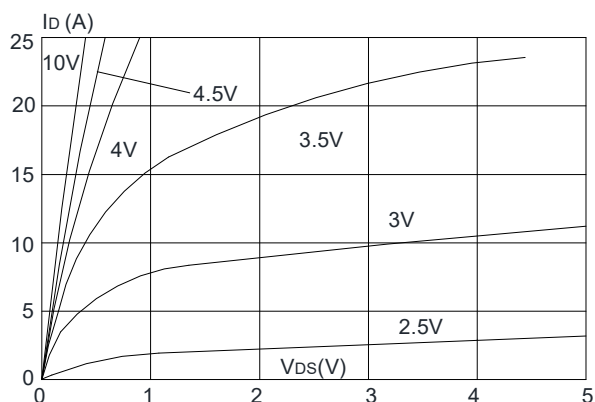


Figure 2: Typical Transfer Characteristics

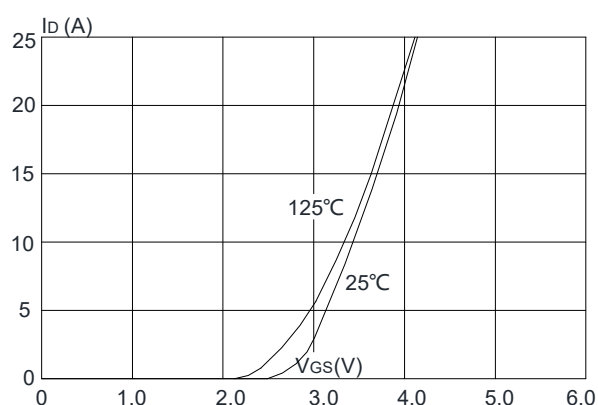


Figure 3: On-resistance vs. Drain Current

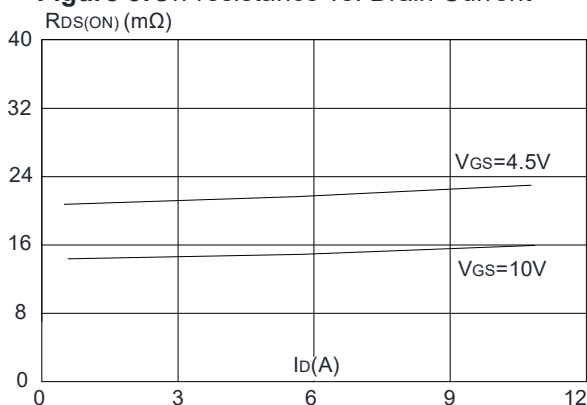


Figure 4: Body Diode Characteristics

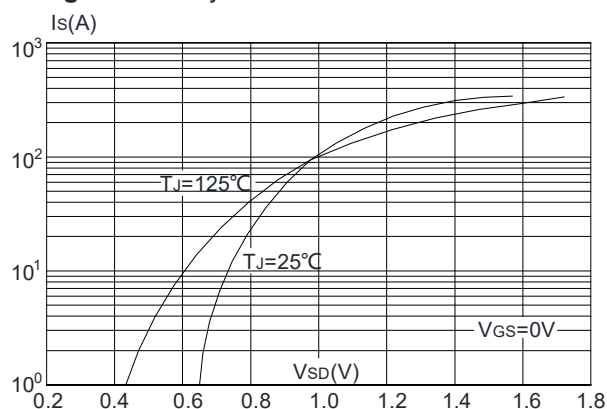


Figure 5: Gate Charge Characteristics

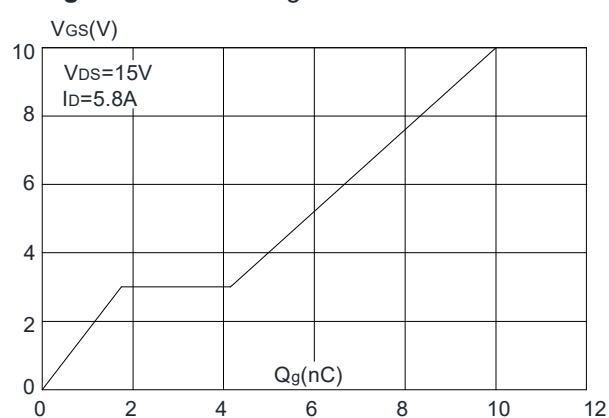
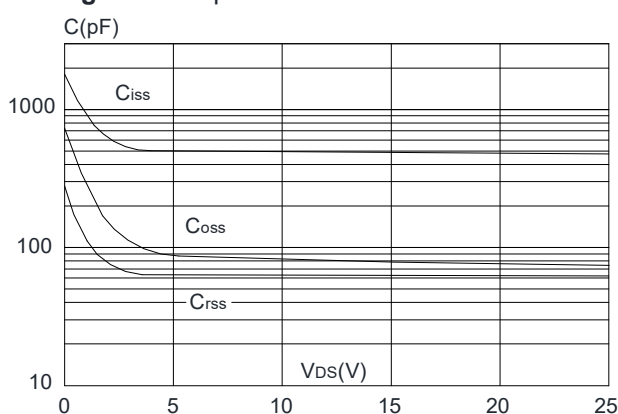


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

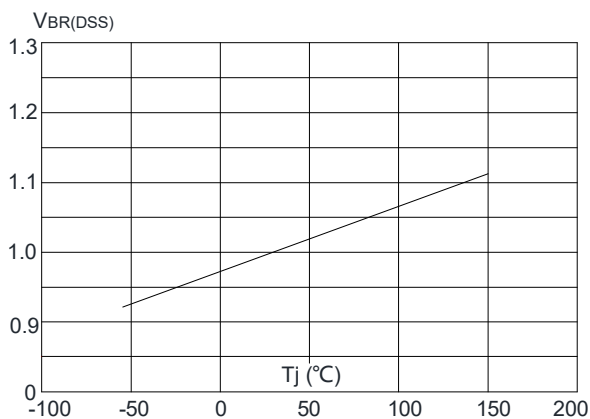


Figure 8: Normalized on Resistance vs. Junction Temperature

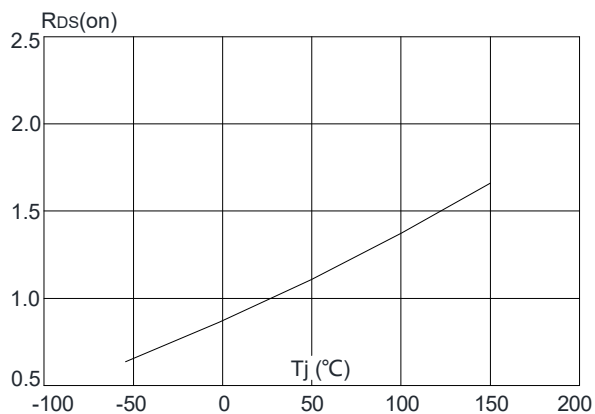


Figure 9: Maximum Safe Operating Area

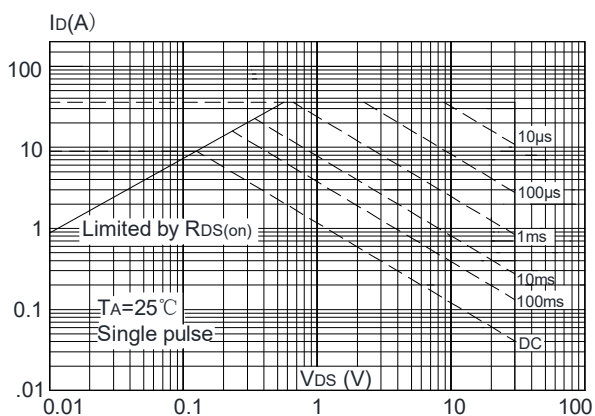


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

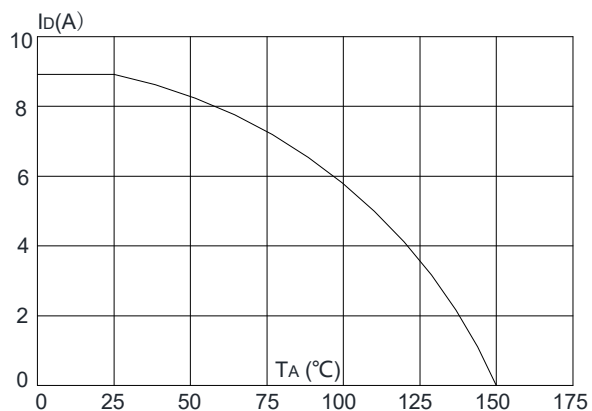
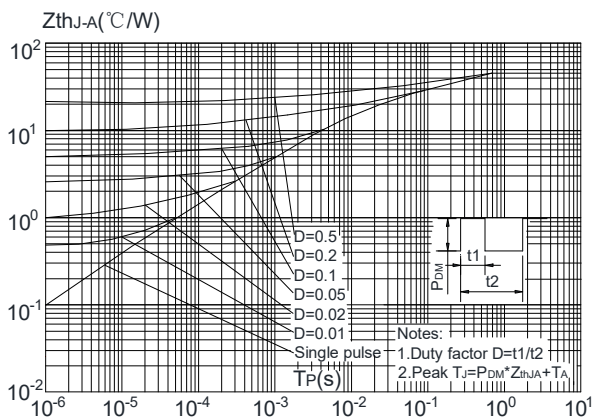


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit

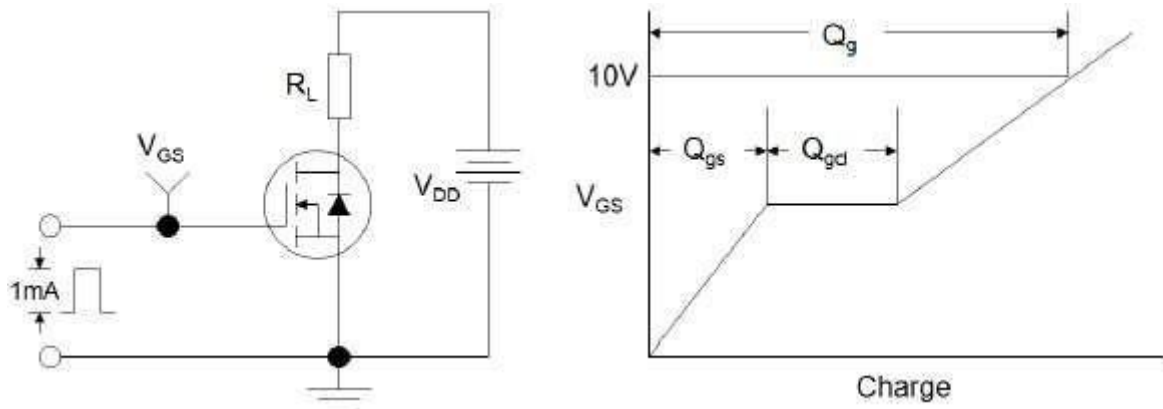


Figure1:Gate Charge Test Circuit & Waveform

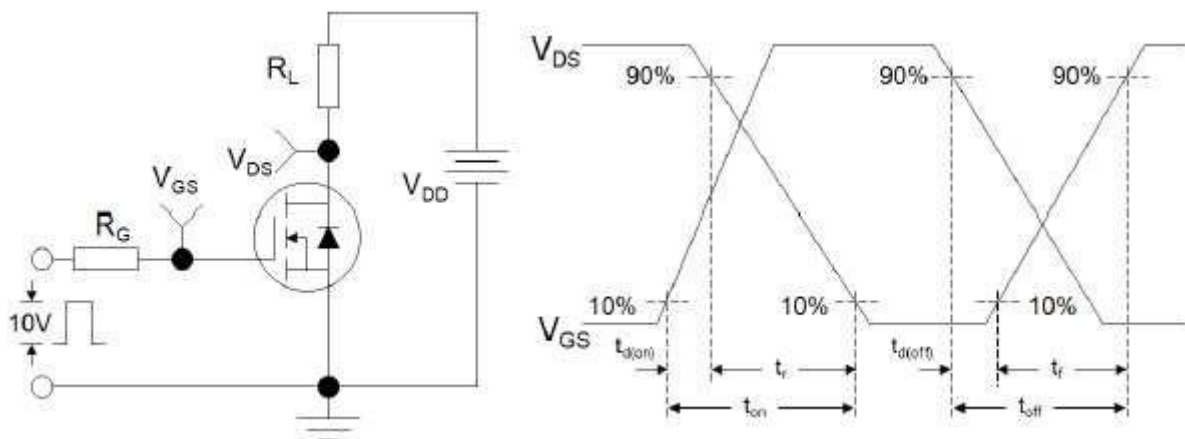


Figure 2: Resistive Switching Test Circuit & Waveforms

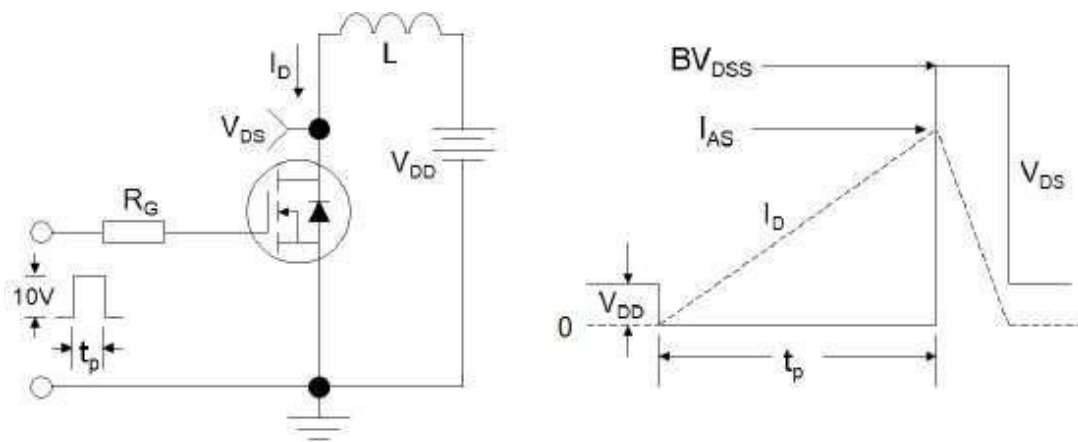
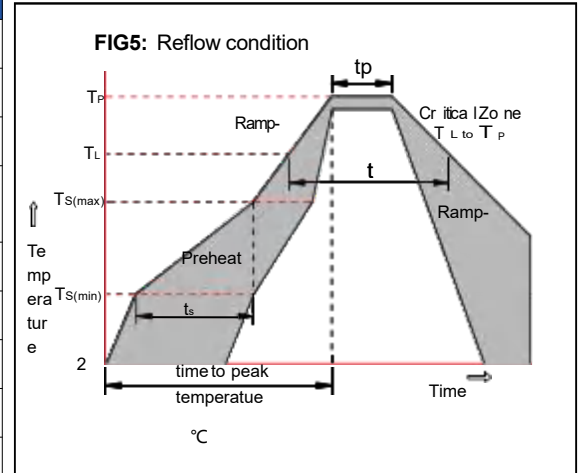


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

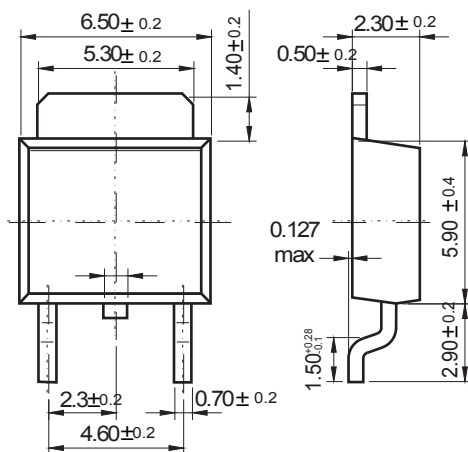
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217 °C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C

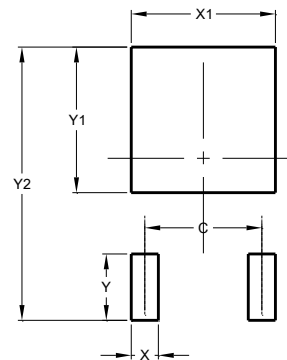


Package Dimensions & Suggested Pad Layout

TO-252



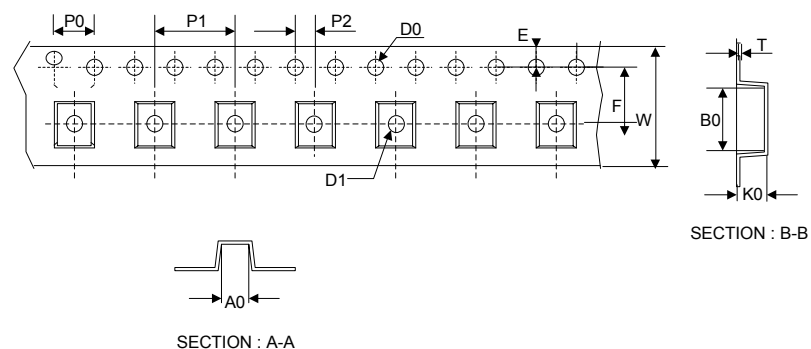
Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	4.55
X	1.50
X1	5.80
Y	2.70
Y1	6.00
Y2	10.90

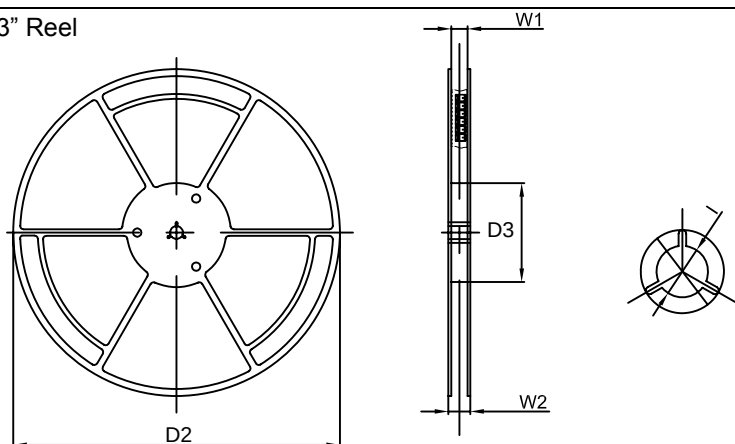
Tape & reel specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.55±0.15
D1	1.55±0.20
E	1.75±0.20
F	7.50±0.20
W	16.00±0.20
A0	7.10±0.20
B0	10.50±0.20
K0	2.70±0.20
T	0.30±0.10
D2	330.0±5.0
D3	100.0±4.0
W1	20.0±5.0
W2	25.0±5.0
I	13.0±2.0

13" Reel



Quantity: 2500PCS